

STARPOWER

SEMICONDUCTOR

IGBT

GD150HFY120C2S

1200V/150A 2 in one-package

General Description

STARPOWER IGBT Power Module provides ultra low conduction loss as well as short circuit ruggedness. They are designed for the applications such as general inverters and UPS.

Features

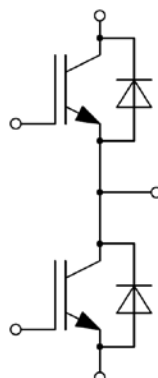
- Low $V_{CE(sat)}$ Trench IGBT technology
- 10 μ s short circuit capability
- $V_{CE(sat)}$ with positive temperature coefficient
- Maximum junction temperature 175°C
- Low inductance case
- Fast & soft reverse recovery anti-parallel FWD
- Isolated copper baseplate using DBC technology



Typical Applications

- Inverter for motor drive
- AC and DC servo drive amplifier
- Uninterruptible power supply

Equivalent Circuit Schematic



Absolute Maximum Ratings $T_C=25^{\circ}\text{C}$ unless otherwise noted**IGBT**

Symbol	Description	Values	Unit
V_{CES}	Collector-Emitter Voltage	1200	V
V_{GES}	Gate-Emitter Voltage	± 20	V
I_C	Collector Current @ $T_C=25^{\circ}\text{C}$	291	A
	@ $T_C=100^{\circ}\text{C}$	150	A
I_{CM}	Pulsed Collector Current $t_p=1\text{ms}$	300	A
P_D	Maximum Power Dissipation @ $T_j=175^{\circ}\text{C}$	1102	W

Diode

Symbol	Description	Values	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	1200	V
I_F	Diode Continuous Forward Current	150	A
I_{FM}	Diode Maximum Forward Current $t_p=1\text{ms}$	300	A

Module

Symbol	Description	Value	Unit
T_{jmax}	Maximum Junction Temperature	175	$^{\circ}\text{C}$
T_{jop}	Operating Junction Temperature	-40 to +150	$^{\circ}\text{C}$
T_{STG}	Storage Temperature Range	-40 to +125	$^{\circ}\text{C}$
V_{ISO}	Isolation Voltage RMS, $f=50\text{Hz}$, $t=1\text{min}$	4000	V

IGBT Characteristics $T_c=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit	
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C=150\text{A}, V_{GE}=15\text{V}, T_j=25^\circ\text{C}$		1.70	2.15	V	
		$I_C=150\text{A}, V_{GE}=15\text{V}, T_j=125^\circ\text{C}$		1.95			
		$I_C=150\text{A}, V_{GE}=15\text{V}, T_j=150^\circ\text{C}$		2.00			
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C=3.75\text{mA}, V_{CE}=V_{GE}, T_j=25^\circ\text{C}$	5.2	6.0	6.8	V	
I_{CES}	Collector Cut-Off Current	$V_{CE}=V_{CES}, V_{GE}=0\text{V}, T_j=25^\circ\text{C}$			1.0	mA	
I_{GES}	Gate-Emitter Leakage Current	$V_{GE}=V_{GES}, V_{CE}=0\text{V}, T_j=25^\circ\text{C}$			400	nA	
R_{Gint}	Internal Gate Resistance			5.0		Ω	
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600\text{V}, I_C=150\text{A}, R_G=1.1\Omega, V_{GE}=\pm 15\text{V}, T_j=25^\circ\text{C}$		123		ns	
t_r	Rise Time			27		ns	
$t_{d(off)}$	Turn-Off Delay Time			407		ns	
t_f	Fall Time			66		ns	
E_{on}	Turn-On Switching Loss				5.35		mJ
E_{off}	Turn-Off Switching Loss				11.0		mJ
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600\text{V}, I_C=150\text{A}, R_G=1.1\Omega, V_{GE}=\pm 15\text{V}, T_j=125^\circ\text{C}$		139		ns	
t_r	Rise Time			32		ns	
$t_{d(off)}$	Turn-Off Delay Time			495		ns	
t_f	Fall Time			116		ns	
E_{on}	Turn-On Switching Loss				9.63		mJ
E_{off}	Turn-Off Switching Loss				16.5		mJ
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600\text{V}, I_C=150\text{A}, R_G=1.1\Omega, V_{GE}=\pm 15\text{V}, T_j=150^\circ\text{C}$		144		ns	
t_r	Rise Time			32		ns	
$t_{d(off)}$	Turn-Off Delay Time			528		ns	
t_f	Fall Time			138		ns	
E_{on}	Turn-On Switching Loss				10.7		mJ
E_{off}	Turn-Off Switching Loss				17.6		mJ
I_{SC}	SC Data	$t_P \leq 10\mu\text{s}, V_{GE}=15\text{V}, T_j=150^\circ\text{C}, V_{CC}=900\text{V}, V_{CEM} \leq 1200\text{V}$		600		A	

Diode Characteristics $T_C=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_F	Diode Forward Voltage	$I_F=150\text{A}, V_{GE}=0\text{V}, T_j=25^{\circ}\text{C}$		1.65	2.10	V
		$I_F=150\text{A}, V_{GE}=0\text{V}, T_j=125^{\circ}\text{C}$		1.65		
		$I_F=150\text{A}, V_{GE}=0\text{V}, T_j=150^{\circ}\text{C}$		1.65		
Q_r	Recovered Charge	$V_R=600\text{V}, I_F=150\text{A},$ $-di/dt=5800\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=25^{\circ}\text{C}$		13.3		μC
I_{RM}	Peak Reverse Recovery Current			209		A
E_{rec}	Reverse Recovery Energy			6.65		mJ
Q_r	Recovered Charge	$V_R=600\text{V}, I_F=150\text{A},$ $-di/dt=5800\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=125^{\circ}\text{C}$		23.8		μC
I_{RM}	Peak Reverse Recovery Current			228		A
E_{rec}	Reverse Recovery Energy			10.9		mJ
Q_r	Recovered Charge	$V_R=600\text{V}, I_F=150\text{A},$ $-di/dt=5800\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=150^{\circ}\text{C}$		26.6		μC
I_{RM}	Peak Reverse Recovery Current			238		A
E_{rec}	Reverse Recovery Energy			12.8		mJ

Module Characteristics $T_C=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Min.	Typ.	Max.	Unit
L_{CE}	Stray Inductance			20	nH
$R_{CC'+EE'}$	Module Lead Resistance, Terminal to Chip		0.35		m Ω
R_{thJC}	Junction-to-Case (per IGBT)			0.136	K/W
	Junction-to-Case (per Diode)			0.313	
R_{thCH}	Case-to-Heatsink (per IGBT)		0.029		K/W
	Case-to-Heatsink (per Diode)		0.066		
	Case-to-Heatsink (per Module)		0.010		
M	Terminal Connection Torque, Screw M6	2.5		5.0	N.m
	Mounting Torque, Screw M6	3.0		5.0	
G	Weight of Module		300		g

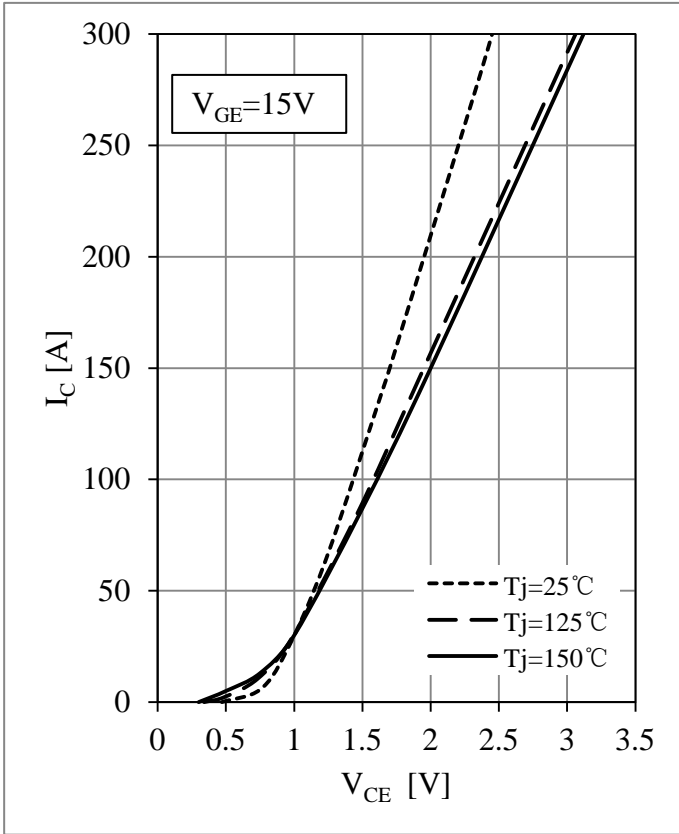


Fig 1. IGBT Output Characteristics

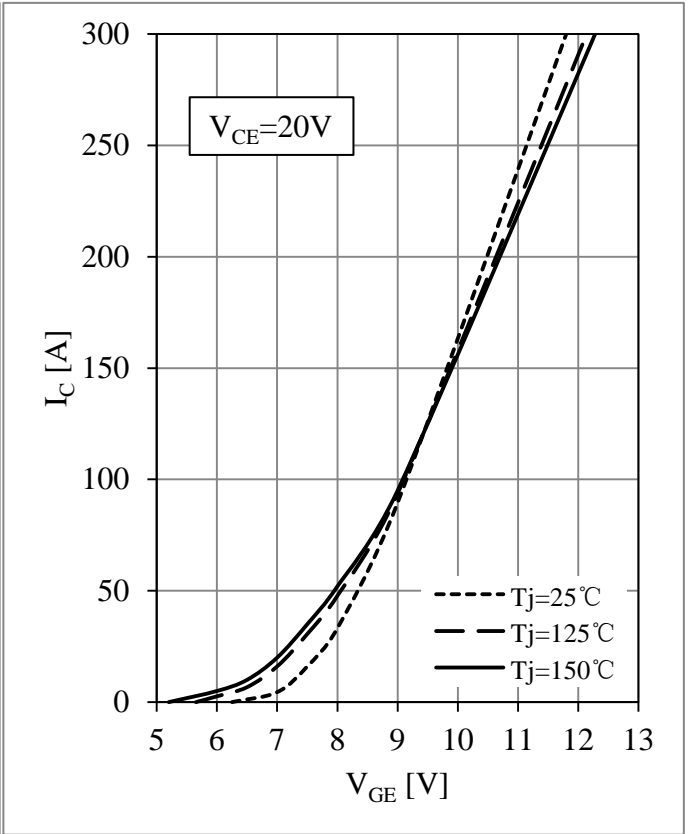


Fig 2. IGBT Transfer Characteristics

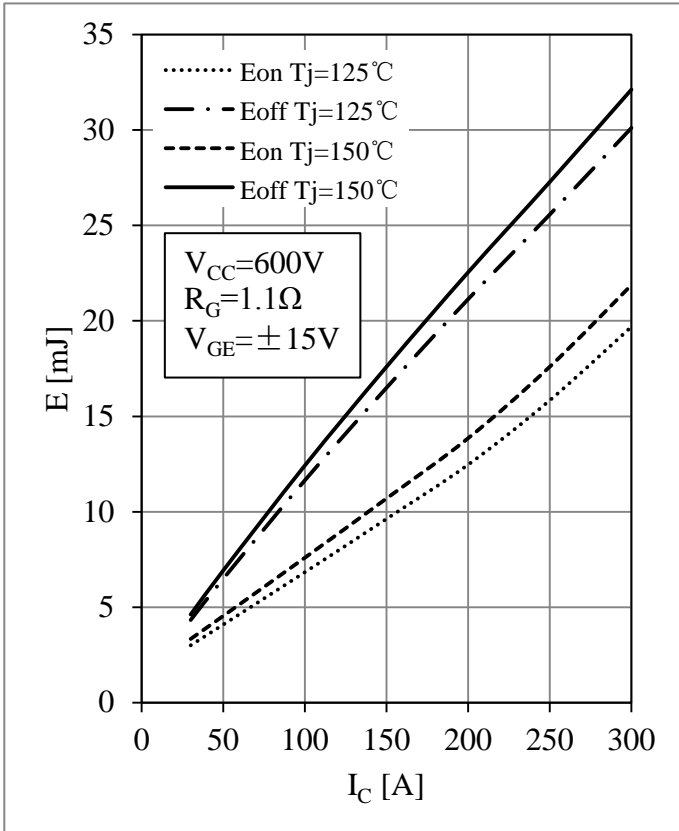


Fig 3. IGBT Switching Loss vs. I_C

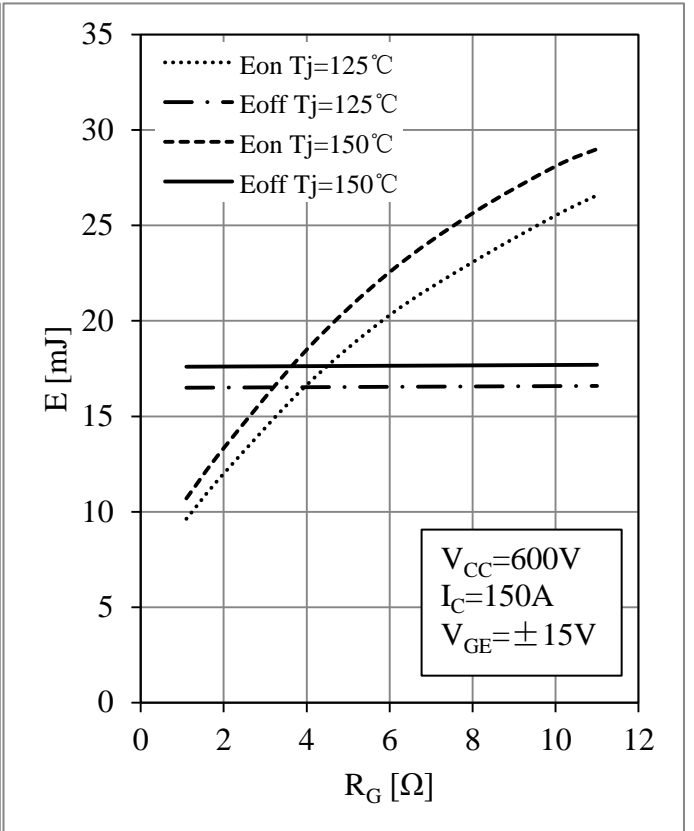


Fig 4. IGBT Switching Loss vs. R_G

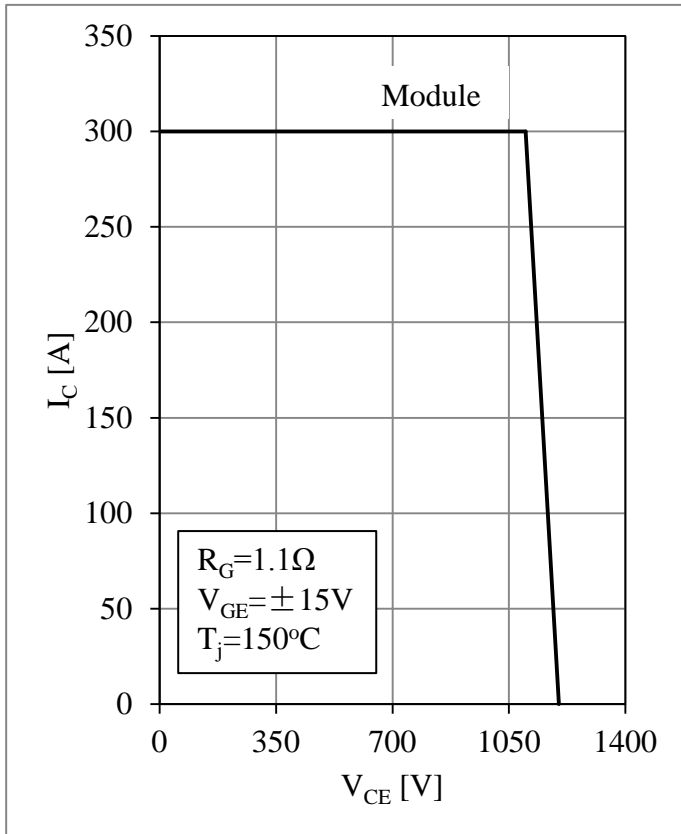


Fig 5. RBSOA

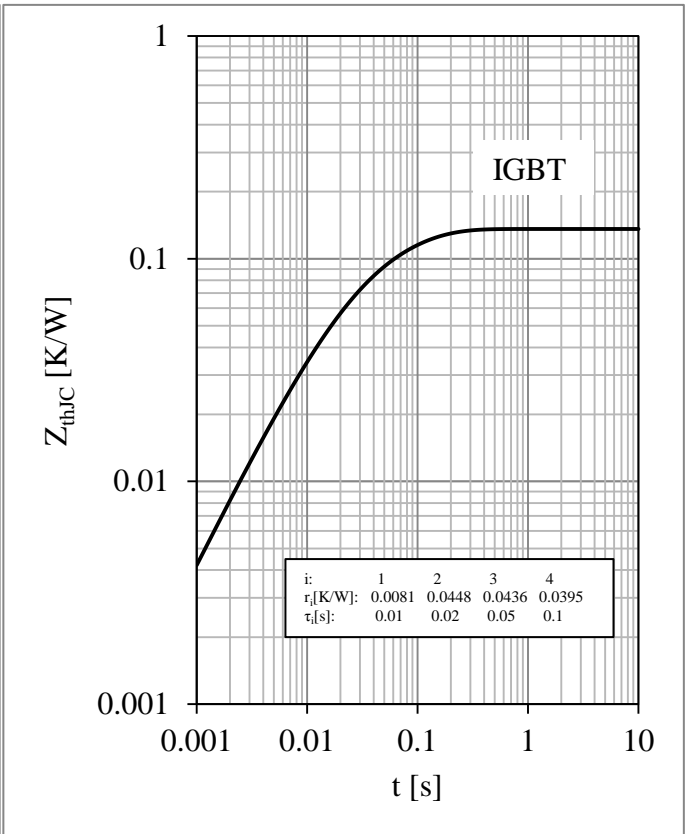


Fig 6. IGBT Transient Thermal Impedance

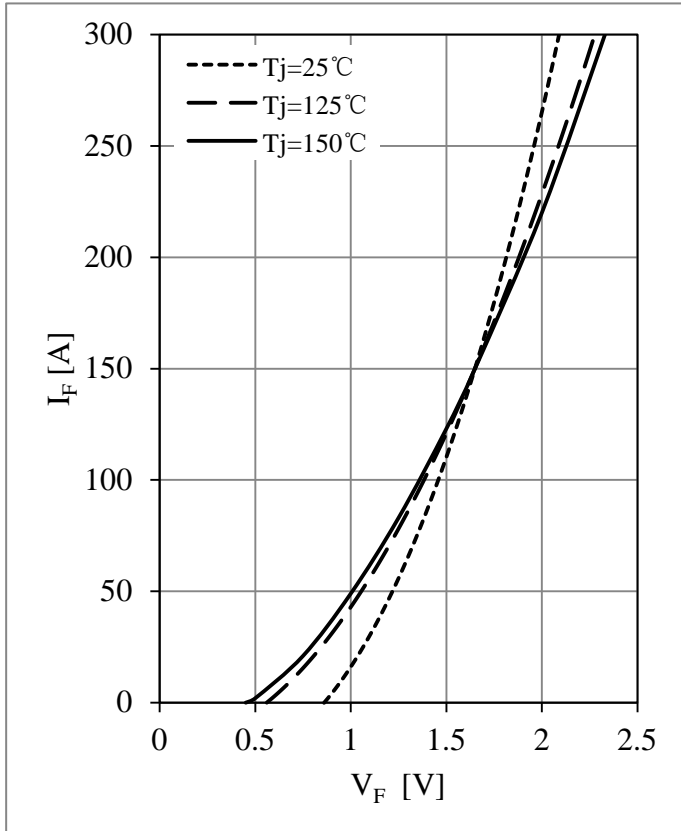


Fig 7. Diode Forward Characteristics

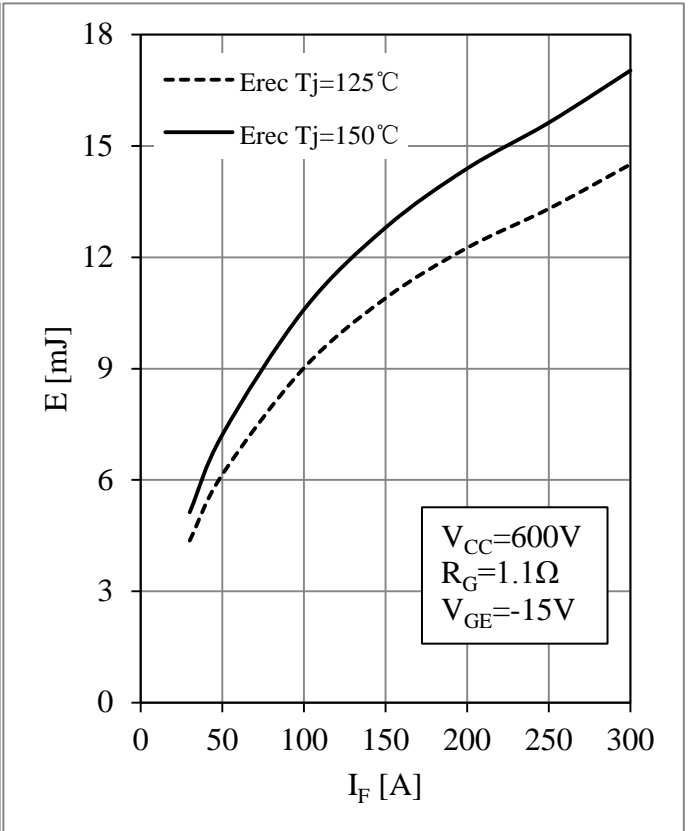


Fig 8. Diode Switching Loss vs. I_F

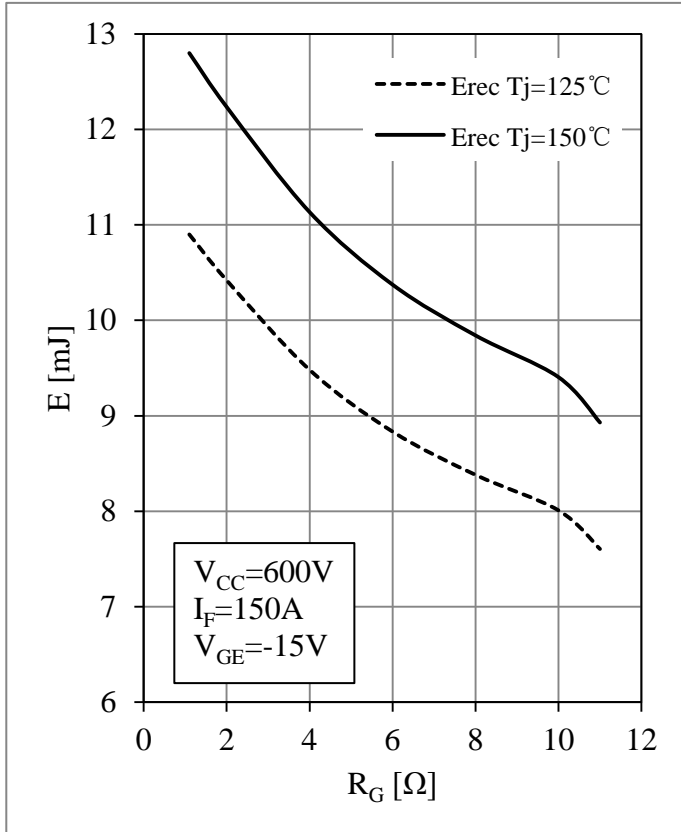


Fig 9. Diode Switching Loss vs. R_G

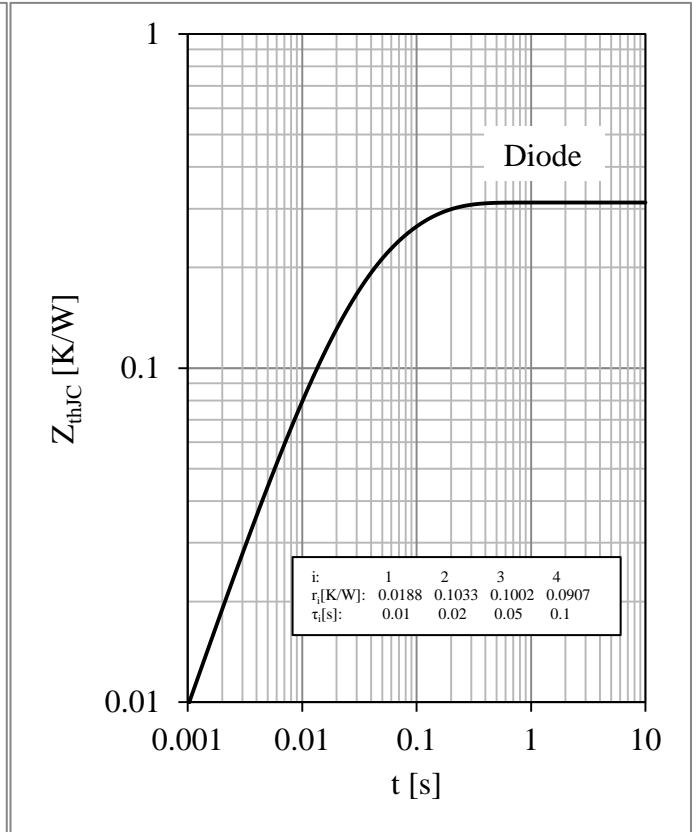


Fig 10. Diode Transient Thermal Impedance

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